

FEATURES

- For general purpose applications
- Metal-on-silicon junction Schottky barrier which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications
- These diodes are also available in the Mini-MELF case with type designation LL6263, in the Micro-MELF case with type designation MCL6263

MECHANICAL DATA

- **Case:** DO-35 Glass CASE
- **Polarity:** Color band denotes cathode end
- **Weight:** Approx. 0.13gram

DO-35



Dimensions in inches and (millimeters)

ABSOLUTE RATINGS(LIMITING VALUES)

	SYMBOLS	VALUE	UNITS
Peak Reverse Voltage	V_{RRM}	60	V
Power Dissipation (infinite Heat Sink)	P_{tot}	400	mW
Maximum Single cycle surge 10 μ s square wave	I_{FSM}	2.0	A
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

	SYMBOLS	Min.	TYP.	MAX.	UNITS
Reverse Breakover Voltage at $I_R=10\mu A$	V_R	60			V
Leakage Current at $V_R=50V$	I_R			200	nA
Forward voltage drop at $I_F=1mA$ $I_F=15mA$	V_F			0.41 1.0	V
Junction Capacitance at $V_R=0V, f=1MHz$	C_J			2.0	pF
Reverse Recovery time at $I_F=I_R=5mA$, recover to 0.1 I_R	T_{rr}			1	ns
Thermal resistance	$R_{\theta JA}$			0.3	K/W

Fig.1 Typical variation of forward Current vs forward voltage for primary conduction through the Schottky barrier

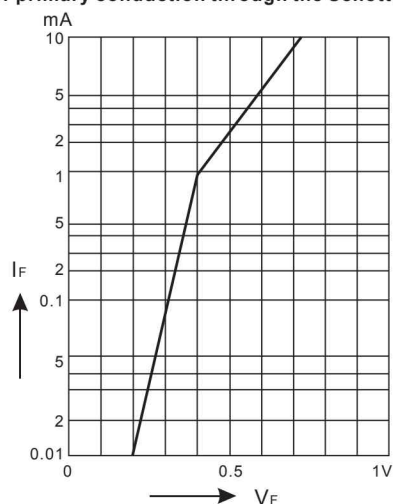


Fig.2 Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

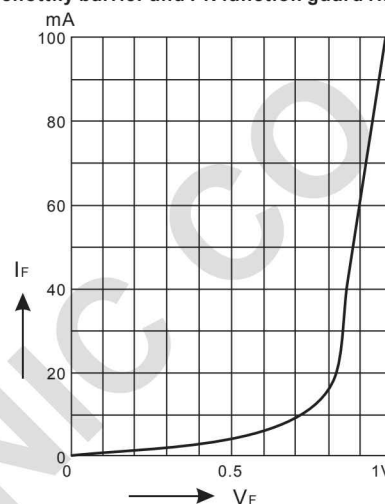


Fig.3 Typical variation of reverse current at various temperatures

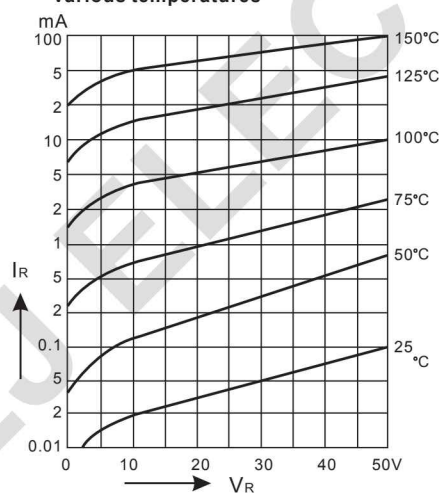


Fig.4 Typical variation curve as a function of reverse voltage

